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## **FEATURES**

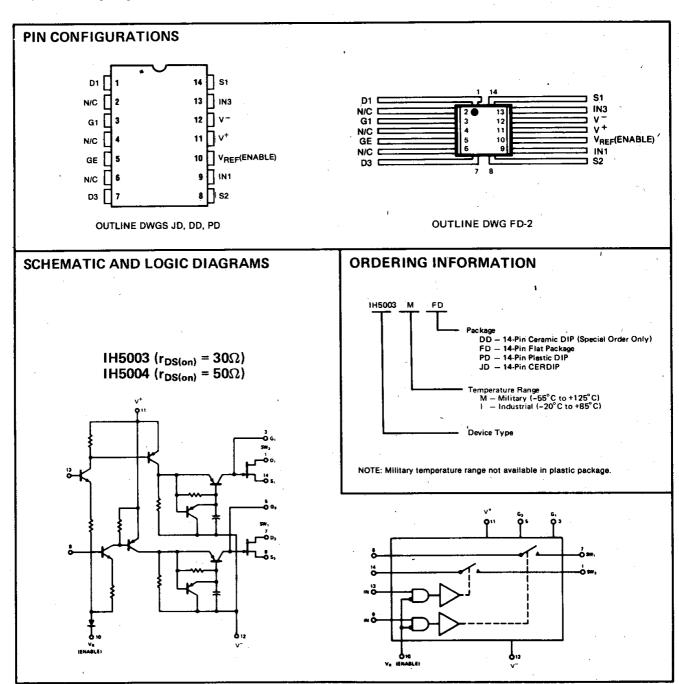
- Gate Lead Available for Nulling Charge Injection Voltage
- Each Channel Complete—Interfaces With Most Integrated Logic
- Low OFF Power Dissipation, —1 mW
- Switches Analog Signals up to 20 Volts Peak-to-Peak
- Low r<sub>DS(ON)</sub>, 30Ω Max on IH5003

## **GENERAL DESCRIPTION**

These switching circuits contain two channels in one package, each channel consisting of a driver circuit controlling a SPST junction FET switch. The driver interfaces DTL, TTL, or RTL logic signals for multiplexing, commutating,

# IH5003/IH5004 2-Channel Drivers with SPST FET Switches AND Gate Available

and D/A converter applications, which permits logic design directly with the switch function. Logic "1" at the input turns the FET switch ON, and logic "0" turns it OFF. The gate lead of the FETs has been brought out to enable the application of a referral resistor for nulling out offset voltage due to charge injection.



# IH5003/5004

# **ABSOLUTE MAXIMUM RATINGS**

Analog Signal Voltage $(V_A - V^- \text{ or } V^+ - V_A)$	30V
Total Supply Voltage (V <sup>+</sup> - V <sup>-</sup> )	36V
Pos. Supply Voltage to Ref. Voltage (V+ - VR)	25V
Ref. Voltage to Neg. Supply Voltage (V <sub>R</sub> - V <sup>-</sup> )	22V
Power Dissipation (Note)	750 mW
Current (Any Terminal)	30 mA
Storage Temperature -65 to	5+150°C
Operating Temperature -55 to	o +125°C
Lead Temperature (Soldering, 10 sec)	300°C

NOTE: Dissipation rating assumes device is mounted with all leads welded or soldered to printed circuit board in ambient temperature below 70°C. For higher temperature, derate at rate of 10 mW/°C.

Stresses above those listed under Absolute Maximum Ratings may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions above those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

## **ELECTRICAL CHARACTERISTICS**

Applied Voltages for all tests:  $V^+ = +12V$ ,  $V^- = -18V$ , GND = 0. Input test condition which guarantees FET switch ON or OFF as specified is used for output and power supply specifications.

	SYMBOL	TYPE	ABSOLUTE MAX LIMIT			UNITS	TEST CONDITIONS	
	(NOTE)	CHARACTERISTIC	ITPE	-55°	25°	126°	UNITS	120. 03.13.7.13.10
-Z4.3H	VIN(ON)	Input Voltage-ON		2.9 min	2.5 min	2.0 min	Volts	V <sup>-</sup> = -12V
	VINIOFFI	Input Voltage-OFF	Both	1.4	1.0	0.6	Volts	V- = -12V
	INION	Input Current	Circuits	120	60	60	μΑ	V <sub>IN</sub> = 2.5V
	<sup>1</sup> IN(OFF)	Input Leakage Current	1	0.1	0.1	2	μΑ	V <sub>IN</sub> = 0.8V
02-IO€0 	PDS(ON) Drain-Source ON Resistance	IH5003	30	30	50	Ω	V <sub>D</sub> = 10V, I <sub>S</sub> = 1 mA	
		H5004	50	50	85	Ω		
	ID (ON) + IS (ON)	Drive Leakage Current	Both Circuits		2	100	nA	V <sub>D</sub> = V <sub>S</sub> = -10V
	IS(OFF)	Source Leakage Current			1	100	nA	V <sub>S</sub> = 10V, V <sub>D</sub> = -10V
	ID(OFF)	Drain Leakage Current			1	100	nA	$V_0 = 10V, V_S = -10V$
POWER SUPPLY	1+	Positive Power Supply Drain Current	Both Circuits		3		mA	One Driver ON, V <sub>IN</sub> = 2.5V  Both Drivers OFF V <sub>IN</sub> = 0.8V
	1-	Negative Power Supply Drain Current			-1.8		mA	
	IREF	Reference Power Sup- ply Drain Current			-1.4		mA	
	1 <sup>+</sup> LK	Positive Power Supply Leakage Current			25		μΑ	
	I-IK	Negative Power Supply Leakage Current			-25		μΑ	
	RLK	Reference Power Sup- ply Leakage Current			-25		μА	
ME-FUI P.OSWE	ton	Turn-ON Time	Both Circuits		0.3	0.5	μς	See Below
	toff	Turn-OFF Time			0.8	1.2	μs	
	Pon	ON Driver Power	Both		175		mW	Both inputs V <sub>IN</sub> = 2.5
	Poff	OFF Driver Power	Circuits		1	<u> </u>	mW	Both Inputs V <sub>IN</sub> = 1V
F E T	V <sub>GS(f)</sub>	Gate Source Forward Voltage	Both Circuits		1.5		Volts	I <sub>G</sub> = 1.0 mA, V <sub>DS</sub> = 0

NOTE: (OFF) and (ON) subscript notation refers to the conduction state of the FET switch for the given test.

